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Picosecond timing resolution with 3D trench silicon sensors







High Luminosity and Future Colliders

Extremely high instantaneous luminosity planned at today's upgraded and future colliders:

- High radiation damage to tracking detectors
- **Difficult event reconstruction** due to large pile-up, implied by:
 - Association of traces to a certain Primary Vertex 0
 - Correct pattern recognition 0

Spatial resolution Time resolution Radiation hardness





All required at the same time!

FCC-hh (20??) requirements:

 $-\sigma_{t} = 10-20 \text{ ps}$

$$-\sigma_s = 10 \ \mu m$$

$$-F = 10^{17}$$
 to 10^{18} 1 MeV n_{ed}





Original idea by S. Parker, 1997



- Short inter-electrode drift distance: extremely fast signals
- Active volume and **electrode shape** can be **designed for** maximum performance
- Unmatched radiation hardness (> 10^{17} 1 MeV n_{eq}/cm²) NIMA, 979 (2020) 164458
 - 3D columnar geometry is a production-ready technology (ATLAS IBL, ATLAS-P2)







The optimized 3D sensor design

Current signal is defined as (Ramo's theorem):



Electrode shape optimization allows the signals to be independent of the hit position







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• 55x55 μ m² pixels (compatible with existing FEE)

In each pixel a 40 μ m long n++ trench is placed between the continuous p++ trenches for the bias

150 μ **m active thickness**, on a 350 μ m-thick support wafer

Collection electrode **135** µm deep







The Fabrication Process

Two batches were produced in 2019 and 2021 at Fondazione Bruno Kessler (FBK, Trento, Italy) using the Deep Reactive Ion Etching (DRIE) Bosch process, 6" wafers.

Many devices were designed and fabricated, such as:











SEM HV: 10.0 kV	WD: 11.59 mm		VEGA3
View field: 176 µm	Det: SE	50 µm	
SEM MAG: 1.57 kx	Date(m/d/y): 10/29/19	FBK Micro-	nano Faci





Tested devices: timing and efficiency

- Different devices were tested at **SPS/H8** (November 2021, May 2022)
- Custom made front-end electronic boards featuring a two stage transimpedance amplifier



1 PIXEL

1 STRIP (10 pixels)

3 **5** | **KIPS** (30 pixels)





SPS beam test: Experimental Setup

- **180 GeV/c** π^+ beam, 10⁶ pions per spill on a beam spot of 8mm RMS transverse size
- 2 MCP-PMTs on the beam line to time-stamp the arriving particle ($\sigma_{avg} = 5-7 \text{ ps}$)
- One sensor fixed (sensor 1), one sensor mounted on **piezoelectric stages** (sensor 2) to precisely align the two 3D structures, all mounted in a RF-shielded box
- Possibility of operating the fixed sensor down to -40°C using dry ice to test irradiated devices.
- Readout with 8GHz bandwidth 20GS/s Scope, trigger on the AND of one 3D sensor and one of the MCP-PMTs









Waveforms Analysis

For each waveform:

- Signal baseline is evaluated on an event-by-event basis
- The signal amplitude A is measured (w.r.t. to the baseline)
- Signal time of arrival evaluated with various methods:
 - Leading edge: time at 15 mV signal amplitude
 - Spline: a CFD at 35% with rising edge interpolated with a spline
 - **Reference:** subtract each waveform from a delayed (by half of 0 the signal rise time) copy of itself, then on the resulting signal we trigger at X/2 height





3D pixel: amplitude performance

NON-IRRADIATED PIXEL



- Normal incidence
- The pixel (DUT) is not on the trigger
- Good sensor performance at low bias voltage





3D pixel: timing performance



- Symmetric time distribution, with only a small tail due to late signals
- (no time walk correction)

Time distribution fitted with two gaussians to include late signals contributions

• Excellent performance with CFD-based methods, but also using leading edge algorithm



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The trenches are non-active volumes:

to **tilt the sensor** with respect to normal incidence is needed to recover the geometrical efficiency

To measure efficiency:

- Trigger on a single pixel ($55x55\mu$ m²) centered on a triple strip (165x550 μ m²) and counting the fraction of signals seen in the triple strip
- The single **pixel** is mounted on the **piezoelectric** stages, the triple strip has fixed position but can rotate around the trench direction

Efficiency tests: the setup









F. Borgato



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Efficiency tests: the method



- the number of events in time (populating the peak) over the total number of trigger events
- of active area ($\approx 80\%$)



• From the time distribution of the triple strip signals w.r.t the MCP-PMTs, the efficiency is computed by

3D pixel detection (geometrical) efficiency at normal incidence is in agreement with calculated fraction





Efficiency tests: the results



Efficiency vs tilt-angle



The inefficiency (at normal incidence) due to the dead-area of the trenches is fully recovered by tilting the sensors around the trench axis at angles larger than 10°





Tilted sensors: timing performances







Radiation hardness of 3D-trench silicon sensor studies

- **3D sensors irradiated** at the Triga Mark II reactor at the Jožef Stefan Institute in Lubjiana, Slovenia
- Fluences: up to $2.5 \cdot 10^{16}$ 1 MeV n_{eq}/cm²

innermost detectors

- Sensors tested below -20°C to reduce leakage current
- Efficiency and timing studies performed in the irradiated sensors as well













Irradiated sensors: amplitude performance



Larger bias voltage is required to recover the signal amplitude for irradiated sensors





Irradiated sensors: timing





$2.5 \cdot 10^{16}$ 1 MeV n_{eq}/cm² - 0°

11 **Excellent time resolution** measured at 150V on single pixel irradiated 2.5 $\cdot 10^{16}$ 1 MeV n_{ea}/cm² !









Irradiated sensors: efficiency

Efficiency [%]



Increasing the irradiated sensor bias voltage to 130V allows to fully recover the efficiency @20° expected for non-irradiated sensors





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Conclusions

- The time resolution of a single 3D-trench pixel sensor was measured at SPS with a 180 GeV/c π^+ beam and found to be about **11 ps** @ V_{bias} =100V (sensor intrinsic + FEE noise)
- The sensor detection efficiency is fully recovered for incident angles larger than 10° with respect to normal incidence
- Sensors irradiated at a fluence of $2.5 \cdot 10^{16}$ 1 MeV n_{eq}/cm² at V_{bias} exceeding 100V perform as the non-irradiated sensors, both in timing performances and efficiency
- **3D devices confirm** their theoretical **excellent performance** in timing and the trench geometry appears to be the right direction to go

The front-end electronics is now the limiting factor to the system performance







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TimeSPOT already developed the Timespot1 28-nm CMOS ASIC 32x32 matrix



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Outlook



Thank you for your attention!

<u>Publications by the TimeSPOT Collaboration</u>

- 3D trenched-electrode sensors for charged particle tracking and timing, NIM A, (2019)
- Simulation of 3D-Silicon sensors for the TIMESPOT project NIMA,936-, (2019)
- Development of 3D trenched-electrode pixel sensors with improved timing performance JINST, 14-, C07011 (2019)
- Sensors, electronics and algorithms for tracking at the next generation of colliders NIMA,927-, (2019)
- Combined TCAD and Geant4 simulations of diamond detectors for timing applications NIMA,936-, (2019)
- and Electronics, 2019
- First results of the TIMESPOT project on developments on fast sensors for future vertex detectors, NIMA, 2020
- Timing characterisation of 3D-trench silicon sensors, JINST, 2020
- Intrinsic time resolution of 3D-trench silicon pixels for charged particle detection, arXiv:2004.10881, JINST, 2020
- High-resolution timing electronics for fast pixel sensors, arXiv:2008.09867, to appear in JINST
- measurements, JINST 16 (2021) 09, P09028.
- Front. Phys. 10:804752. doi: 10.3389/fphy.2022.804752

• A Timing Pixel Front-End Design for HEP Experiments in 28 nm CMOS Technology, 15thConference on Ph.D. Research in Microelectronics

• A. Loiet al., Timing Optimisation and Analysis in the Design of 3D silicon sensors: the TCoDeSimulator, JINST (2021) 16:P02011

• D. Brunduet al., Accurate modelling of 3D-trench silicon sensor with enhanced timing performance and comparison with test beam

• L. Piccolo et al., First Measurements on the Timespot1 ASIC: a Fast-Timing, High-Rate Pixel-Matrix Front-End, arXiv:2201.13138 BrunduD, et al. (2022) Modelingof Solid-State Detectors Using Advanced Multi-Threading: The TCoDeand TFBoostSimulation Packages.



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Static characterization of 3D-trench pixel strips

STRIP 392 (batch1, NO p-spray)



STRIP 392 (batch2, with p-spray)



Limits to the time resolution of a 3D sensor

$$\sigma_t = \sqrt{\sigma_{tw}^2 + \sigma}$$



 $imes \sigma_{dr}$: jitter due to delta-rays - negligible in a 3D sensor since all the charge deposits created at various depths contribute in the same way at the total signal because the charge collection occurs in a direction which is perpendicular to the charged particle path (and in general to the delta-rays produced)

- give the ultimate limit on the time resolution that can be achieved with a 3D sensor

 $imes \sigma_{TDC}$: an adequate TDC will make this term negligible

Physics

etector

Electronics

 $\sigma_{dr}^2 + \sigma_{un}^2 + \sigma_{ej}^2 + \sigma_{TDC}^2$

 $imes \sigma_{tw}$: the time-walk effect can be eliminated by triggering at a constant fraction of the signal amplitude

 σ_{un} : non-uniformities in the weighting field and charge carrier velocities inside the detector sensitive unit

• σ_{ej} : the analog noise of the preamplifier limits the sensor's time resolution and scales as $\approx \frac{\sigma_{noise}}{Amplitude}$

$$\sqrt{\sigma_{un}^2 + \sigma_{ej}^2}$$



Tilted sensors: time distribution





Simulated time of arrival map of a single 3D-trench pixel obtained in the lab by IR laser scan

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In a tilted sensor, every charged track crosses both fast and less-fast regions of the pixels, thus providing a more uniform timing response

Fitting the time distribution: σ_{eff}



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 σ_{eff} is the standard deviation of the mixture distribution of two gaussians:

$$\sigma_t^{eff})^2 = f_1 \cdot (\sigma_1^2 + \mu_1^2) + (1 - f_1) \cdot (\sigma_2^2 + \mu_2^2) - \mu_2^2$$

where f_1 is the fraction of the gaussian core and μ is defined as:

$$\mu = f_1 \cdot \mu_1 + (1 - f_1) \cdot \mu_2$$





Work in progress: charge sharing



Tilting the sensor (Rotation 2) it is possible to study the **behavior of two pixels** (readout on different channels) when a charged particle crosses both.





Work in progress: charge sharing



When a **particle crosses two pixels**, the **sum of the amplitudes** of the two signals is taken.

Combining the whole cluster information (tracks hitting only one pixel + tracks hitting two pixels) it is possible to recover the amplitude distribution expected at normal incidence angle



Work in progress: charge sharing



When a **particle crosses two pixels**, the ToA is the weighted sum on amplitudes of the ToA in the two pixels.

Considering only the tracks hitting two pixels, the σ_t from the weighted mean improves the timing performance when the tracks are equally shared by the two pixels

